

34. A method for manufacturing a semiconductor device, comprising the steps of:  
forming a shallow trench isolation layer in a semiconductor substrate, so that  
active areas and a field area including dummy areas for isolating said active areas are partitioned;  
and

forming gates on said active areas and dummy gates on said dummy areas;  
wherein the shape of at least one said dummy area and/or dummy gate is a circle.

35. A method for manufacturing a semiconductor device, comprising the steps of:  
forming a shallow trench isolation layer in a semiconductor substrate, so that  
active areas and a field area including dummy areas for isolating said active areas are partitioned;  
and

forming gates on said active areas and dummy gates on said dummy areas;  
wherein a plurality of said dummy areas and/or dummy gates are arranged in at  
least two rows and/or two columns.

36. A method as claimed on claim 35, wherein at least one said row is shifted from  
another said row and/or at least one column is shifted from another said column.--

#### REMARKS

The specification has been amended to correct the informality noted by the Examiner,  
and to employ more idiomatic English.

Pursuant to 37 CFR § 1.121, marked portions of the specification showing changes made  
therein accompany this Amendment. No new matter has been entered.

Non-elected claims 1-11 and 24-32 have been cancelled. And, claims 12-23 have been  
canceled and have been replaced with claims 33-36. Claims 33-35 comprise the subject matter  
of former claim 12, combined with that of claims 18, 19 and 20, respectively. Claim 36 has been  
written to incorporate the limitations of former claims 21-23. These claims have been rewritten